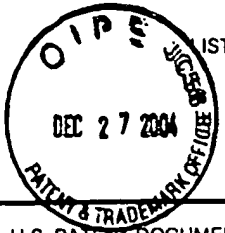

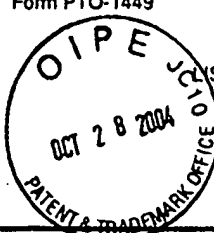


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 <p>LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)</p>				APPLICANT: Garo J. Derderian et al.			
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h	AA	6,753,618	06/2004	Basceri et al.	257	915	
	AB	5,470,794	11/1995	Anjum	437	200	
	AC	2003/0219942 A1	11/2003	Choi et al.	438	253	
	AD	2004/0245560 A1	12/2004	Pontoh et al.	257	309	
	AE	2004/0245559 A1	12/2004	Pontoh et al.	257	306	
	AF	2004/0046197 A1	03/2004	Basceri et al.	257	296	
	AG	2004/0043228 A1	03/2004	Derderian et al.	428	446	
	AH	2003/0213987 A1	11/2003	Basceri et al.	257	296	
h	AI	2003/0205729 A1	11/2003	Basceri et al.	257	200	
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	Document Number	Date	Country	Class	Subclass	Translation	
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
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EXAMINER <i>Quoc H. Ong</i>		DATE CONSIDERED <i>3/2/05</i>					
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 OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT: Garo J. Derderian et al.			
				FILING DATE October 20, 2003		GROUP 2812	
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*Examiner's Initials	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
aa	10/932,218		Basceri et al.	1	1	09/01/04	
ab							
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hu	AA	3,349,474	12/1963	D. H. Rauscher			
	AB	5,904,517	05/1999	Gardner et al.	438	197	
	AC	5,998,264	12/1999	Wu	438	260	
	AD	6,180,465 B1	01/2001	Gardner et al.	438	291	
	AE	6,207,485 B1	03/2001	Gardner et al.	438	216	
hu	AF	6,548,854 B1	04/2003	Kizilyalli et al.	257	310	
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hu	AH	2003/0045060 A1	03/2003	Ahn et al.	438	287	
hu	AI	2003/0045078 A1	03/2003	Ahn et al.	438	585	
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hu	AJ	EP 0 851 473 A2	01/1998	EPO			X
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hu	AM	Chang et al., Silicon surface treatments in advanced MOS gate processing, Microelectronic Engineering, (2004), pages 130-135					
hu	AN	Lemberger et al., Electrical characterization and reliability aspects of zirconium silicate films obtained from novel MOCVD precursors, Microelectronic Engineering (2004), pages 315-320					
hu	AO	Lu et al., Effects of the TaN, interface layer on doped tantalum oxide high-k films, VACUUM (2004), pages 1-9.					
EXAMINER <i>Wen Huang</i>		DATE CONSIDERED <i>3/2005</i>					
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	AE						
	AF						
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m	AM	Robertson et al., Atomic structure, band offsets, growth and defects at high-K oxide/Si interfaces, Microelectronic Engineering (2004) pages 112-120					
m	AN	Singh et al., High and Low Dielectric Constant Materials, The Electrochemical Society <i>Interface</i> , Summer 1999, pages 26-30					
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h	AA	4,086,074	04/78	Minot et al.			
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	AC	4,683,645	08/87	Naguib et al.			
	AD	4,693,910	09/87	Nakajima et al.			
	AE	4,766,090	08/88	Coquin et al.			
	AF	5,099,304	03/92	Takemura et al.			
	AG	5,236,865	08/93	Sandhu et al.			
	AH	5,444,024	08/95	Anjum et al.			
h	AI	5,470,784	11/95	Anjum et al.			

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h	AA		ABSTRACT: Basceri et al., Atomic Layer Deposition for Nanoscale CU Metalization, 10 pages (pre-April 2004).
h	AN		En et al., Plasma immersion ion implantation reactor design considerations for oxide charging, 85 SURFACE AND COATINGS TECHNOLOGY 64-69 (1966).
h	AO		Ku et al., The Application of Ion Beam Mixing, Doped Silicide, and Rapid Thermal Processing of Self-Aligned Silicide Technology, 137 J. Electrochem. Soc. No. 2, pp. 728-740 (February 1990).

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h	AA	5,670,298	09/97	Hur			
	AB	6,037,239	03/00	Jennings			
	AC	6,096,621	08/00	Jennings			
	AD	6,130,140	10/00	Gonzalez			
	AE	6,133,105	10/00	Chen et al.			
	AF	6,133,116	10/00	Kim et al.			
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	AH	6,277,709 B1	08/01	Wang et al.			
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h	AM		ABSTRACT: How to Eliminate Voiding in Porous-Low-k Dielectrics and The Mechanism of Void Formation; Lin et al.; 4 pages
h	AN		COB Stack DRAM Cell Technology beyond 100 nm Technology Node; Yongjik Park & Kinam Kim; pp. 349.1 - 349.3;
h	AO		Rubin et al., Shallow-Junction Diode Formation by implantation of Arsenic and Boron Through Titanium-Silicide Films and ..., 17 IEEE Transactions on Electron Devices, No. 1, pp. 183-190 (January 1990).

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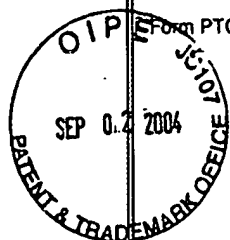
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l	2002/0196651 A1	12/02	Weis	1	1		
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<i>m</i>		10/609,311		Yates			06/03
	AB	10/655,997		Daley			09/03
	AC	10/689,958		Basceri			10/03
	AD	10/882,118		Sandhu et al.			04/04
<i>hw</i>	AE	10/879,367		Blalock et al.			06/04
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